12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN# 20190110000.1
Transfer of select P2-XMOS devices from GFAB to DFAB Wafer Fab site
Change Notification / Sample Request

Date: January 15, 2019
To: TOKYO ELECTRON DEVICE (DSTR) PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

We request you acknowledge receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If you require samples or additional data to support your evaluation, please request within 30 days.

The changes discussed within this PCN will not take effect any earlier than **90** days from the date of this notification, unless customer agreement has been reached on an earlier implementation of the change. This notification period is per TI's standard process.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice, contact your local Field Sales Representative or the PCN Manager (PCN_ww_admin_team@list.ti.com).

PCN Team
SC Business Services

20190110000.1
Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
LM629M-8/NOPB	null

Technical details of this Product Change follow on the next page(s).

PCN Number:	20190110000.1	**PCN Date:**	Jan 15, 2019
Title:	Transfer of select P2-XMOS devices from GFAB to DFAB Wafer Fab site		
Customer Contact:	PCN Manager	**Dept:**	Quality Services
Proposed 1st Ship Date:	Apr 15, 2019	**Estimated Sample Availability:**	Date provided at sample request.

Change Type:		
☐ Assembly Site	☐ Assembly Process	☐ Assembly Materials
☐ Design	☐ Electrical Specification	☐ Mechanical Specification
☐ Test Site	☐ Packing/Shipping/Labeling	☐ Test Process
☐ Wafer Bump Site	☐ Wafer Bump Material	☐ Wafer Bump Process
☒ Wafer Fab Site	☒ Wafer Fab Materials	☒ Wafer Fab Process
	☐ Part number change	

PCN Details

Description of Change:

This change notification is to announce the transfer of select P2-XMOS devices from GFAB to the DFAB (DL-LIN) Wafer Fab site for the selected devices listed in the "Product Affected" section.

Current Fab Site			New Fab Site		
Current Fab Site	**Process**	**Wafer Diameter**	**New Fab Site**	**Process**	**Wafer Diameter**
GFAB6	P2-XMOS	150 mm	DL-LIN	P2-XMOS	200 mm

GFAB6 Die Metallization	DL-LIN Die Metallization
12kA - Al 0.5%Cu	16kA - Al 0.5%Cu

Qual details are provided in the Qual Data Section.

Reason for Change:

Greenock, Scotland (GFAB) Wafer Fab site closure

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Current:

Current Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
GFAB6	GF6	GBR	Greenock

New Fab Site:

New Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DL-LIN	**DLN**	**USA**	**Dallas**

Sample product shipping label (not actual product label)

Product Affected:

LM629M-6/NOPB	LM629M-8/NOPB	LM629MX-8/NOPB	LM629MX-8/S7002371
LM629M-8			

Qualification Report
Approve Date 08-January-2019

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: LM629M-8/NOPB	QBS Process Reference: TLV9002ID
AC	Autoclave (121C, 2atm)	96 Hours	1/77/0	3/231/0
ED	Electrical Characterization	Per Datasheet Parameters	Pass	Pass
ELFR	Early Life Failure Rate, 125C	48 Hours	1/800	3/2400/0
HAST	Biased HAST, 130C/85%RH	96 Hours	-	3/231/0
HBM	ESD - HBM	1000 V	3/9/0	3/9/0
CDM	ESD - CDM	1000 V	3/9/0	3/9/0
HTOL	Life Test, 125C	300 Hours	3/231/0	3/231/0
HTSL	High Temp. Storage Bake, 170C	420 Hours	1/77/0	3/231/0
LU	Latch-up	(per JESD78)	3/18/0	3/18/0
TC	Temperature Cycle, -65/150C	500 Cycles	1/77/0	3/231/0

- QBS: Qual By Similarity
- Qual Device LM629M-8/NOPB is qualified at LEVEL3-260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com